

SOT-563 Plastic-Encapsulate Transistors

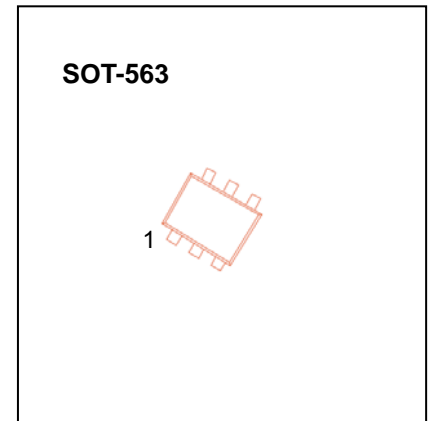
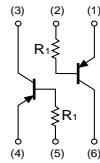
EMB4 General purpose transistors (dual digital transistors)

FEATURES

- Two DTA114T chips in a package

Marking: B4

Equivalent circuit



Absolute maximum ratings (T_a=25°C)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-100	mA
P _C	Collector Power Dissipation	150	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-50μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.5	μA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-1mA	100		600	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA, I _B =-1mA			-0.3	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-5mA, f=100MHz		250		MHz
Input resistance	R ₁	-	7		13	Ω